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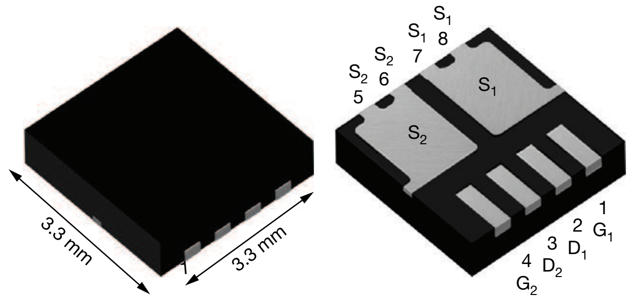
Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

# Common - Drain Dual N-Channel 30 V (S1-S2) MOSFET

**PowerPAK® 1212-8SCD**




Top View    Bottom View

| **PRODUCT SUMMARY** | |
|---|---|
| $V_{S1S2}$ (V) | 30 |
| $R_{S1S2(on)}$ max. (Ω) at $V_{GS}$ = 10 V | 0.005 |
| $R_{S1S2(on)}$ max. (Ω) at $V_{GS}$ = 4.5 V | 0.007 |
| $Q_g$ typ. (nC) | 16.1 [h] |
| $I_{S1S2}$ (A) | 60 [a, g] |
| Configuration | Dual |

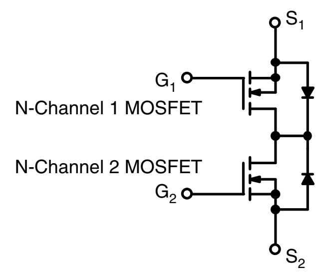
## FEATURES

- TrenchFET® Gen IV power MOSFET
- Very low source-to-source on resistance
- Integrated common-drain n-channel MOSFETs in a compact and thermally enhanced package
- 100 % $R_g$ and UIS tested
- Optimizes circuit layout for bi-directional current flow
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

RoHS COMPLIANT
HALOGEN FREE

## APPLICATIONS

- Battery management
- Load switching




| **ORDERING INFORMATION** | |
|---|---|
| Package | PowerPAK 1212-8SCD |
| Lead (Pb)-free and halogen-free | SiSF00DN-T1-GE3 |

**ABSOLUTE MAXIMUM RATINGS** ($T_A$ = 25 °C, unless otherwise noted)

| PARAMETER | | SYMBOL | LIMIT | UNIT |
|---|---|---|---|---|
| Drain-source voltage | | $V_{S1S2}$ | 30 | V |
| Gate-source voltage | | $V_{GS}$ | +20 / -16 | |
| Continuous drain current ($T_J$ = 150 °C) | $T_C$ = 25 °C | $I_{S1S2}$ | 60 [a] | A |
| | $T_C$ = 70 °C | | 60 [a] | |
| | $T_A$ = 25 °C | | 25.5 [b, c] | |
| | $T_A$ = 70 °C | | 20.4 [b, c] | |
| Pulsed drain current (t = 100 μs) | | $I_{S1S2M}$ | 120 | |
| Maximum power dissipation | $T_C$ = 25 °C | $P_{S1S2}$ | 69.4 | W |
| | $T_C$ = 70 °C | | 44.4 | |
| | $T_A$ = 25 °C | | 5.2 [b, c] | |
| | $T_A$ = 70 °C | | 3.3 [b, c] | |
| Operating junction and storage temperature range | | $T_J$, $T_{stg}$ | -55 to +150 | °C |
| Soldering recommendations (peak temperature) [c] | | | 260 | |

**THERMAL RESISTANCE RATINGS**

| PARAMETER | | SYMBOL | TYPICAL | MAXIMUM | UNIT |
|---|---|---|---|---|---|
| Maximum junction-to-ambient [b] | t ≤ 10 s | $R_{thJA}$ | 19 | 24 | °C/W |
| Maximum junction-to-case (drain) | Steady state | $R_{thJC}$ | 1.4 | 1.8 | |

**Notes**

a. Package limited
b. Surface mounted on 1" x 1" FR4 board
c. t = 10 s
d. See solder profile (www.vishay.com/doc?73257). The PowerPAK 1212-8SCD is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
f. Maximum under steady state conditions is 63 °C/W
g. $T_C$ = 25 °C
h. Single MOSFET

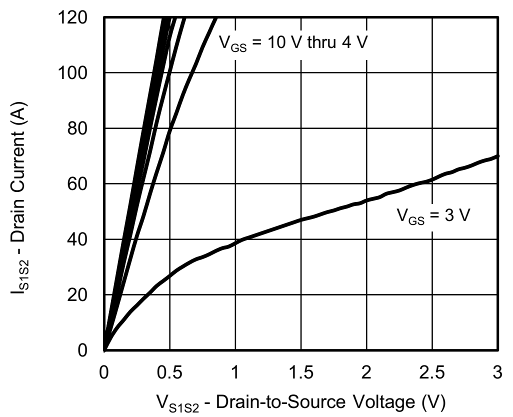
| SPECIFICATIONS ($T_J$ = 25 °C, unless otherwise noted) | | | | | | |
|---|---|---|---|---|---|---|
| **PARAMETER** | **SYMBOL** | **TEST CONDITIONS** | **MIN.** | **TYP.** | **MAX.** | **UNIT** |
| **Static** | | | | | | |
| Drain-source breakdown voltage | $V_{DS}$ | $V_{GS}$ = 0 V, $I_D$ = 250 μA | 30 | - | - | V |
| Gate-source threshold voltage | $V_{GS(th)}$ | $V_{S1S2}$ = $V_{GS}$, $I_D$ = 250 μA | 1 | - | 2.1 | |
| Gate-source leakage | $I_{GSS}$ | $V_{S1S2}$ = 0 V, $V_{GS}$ = +20 / -16 V | - | - | 100 | nA |
| Zero gate voltage drain current | $I_{DSS}$ | $V_{S1S2}$ = 30 V, $V_{GS}$ = 0 V | - | - | 1 | μA |
| | | $V_{S1S2}$ = 30 V, $V_{GS}$ = 0 V, $T_J$ = 70 °C | - | - | 15 | |
| On-state drain current [a] | $I_{S1S2(on)}$ | $V_{S1S2} \geq$ 10 V, $V_{GS}$ = 10 V | 20 | - | - | A |
| Drain-source on-state resistance [a] | $R_{S1S2(on)}$ | $V_{GS}$ = 10 V, $I_{S1S2}$ = 10 A | - | 0.0042 | 0.0050 | Ω |
| | | $V_{GS}$ = 4.5 V, $I_{S1S2}$ = 5 A | - | 0.0056 | 0.0070 | |
| Forward transconductance [a] | $g_{fs}$ | $V_{S1S2}$ = 15 V, $I_{S1S2}$ = 20 A | - | 130 | - | S |
| **Dynamic [b, c]** | | | | | | |
| Input capacitance | $C_{iss}$ | $V_{DS}$ = 15 V, $V_{GS}$ = 0 V, f = 1 MHz | - | 2700 | - | pF |
| Output capacitance | $C_{oss}$ | | - | 865 | - | |
| Reverse transfer capacitance | $C_{rss}$ | | - | 51 | - | |
| Total gate charge | $Q_g$ | $V_{DS}$ = 15 V, $V_{GS}$ = 10 V, $I_D$ =10 A | - | 35 | 53 | nC |
| | | $V_{DS}$ = 15 V, $V_{GS}$ = 4.5 V, $I_D$ = 10 A | - | 16.1 | 24.2 | |
| Gate-source charge | $Q_{gs}$ | | - | 7 | - | |
| Gate-drain charge | $Q_{gd}$ | | - | 2.5 | - | |
| Gate resistance | $R_g$ | f = 1 MHz | 0.3 | 1.5 | 3 | Ω |
| Turn-on delay time | $t_{d(on)}$ | $V_{DD}$ = 15 V, $R_L$ = 1 Ω, $I_{S1S2} \cong$ 10 A, $V_{GEN}$ = 10 V, $R_g$ = 1 Ω | - | 10 | 20 | ns |
| Rise time | $t_r$ | | - | 32 | 65 | |
| Turn-off delay time | $t_{d(off)}$ | | - | 22 | 45 | |
| Fall time | $t_f$ | | - | 10 | 20 | |
| Turn-on delay time | $t_{d(on)}$ | $V_{DD}$ = 15 V, $R_L$ = 1 Ω, $I_D \cong$ 10 A, $V_{GEN}$ = 4.5 V, $R_g$ = 1 Ω | - | 21 | 45 | |
| Rise time | $t_r$ | | - | 60 | 120 | |
| Turn-off delay time | $t_{d(off)}$ | | - | 25 | 50 | |
| Fall time | $t_f$ | | - | 15 | 30 | |
| **Drain-Source Body Diode Characteristics [c]** | | | | | | |
| Continuous source-drain diode current | $I_{S1S2}$ | $T_C$ = 25 °C | - | - | 60 | A |
| Pulse diode forward current | $I_{S1S2M}$ | | - | - | 120 | |
| Body diode reverse recovery time | $t_{rr}$ | $I_F$ = 10 A, di/dt = 100 A/μs, $T_J$ = 25 °C | - | 42 | 85 | ns |
| Body diode reverse recovery charge | $Q_{rr}$ | | - | 42 | 85 | nC |
| Reverse recovery fall time | $t_a$ | | - | 23 | - | ns |
| Reverse recovery rise time | $t_b$ | | - | 19 | - | |

**Notes**

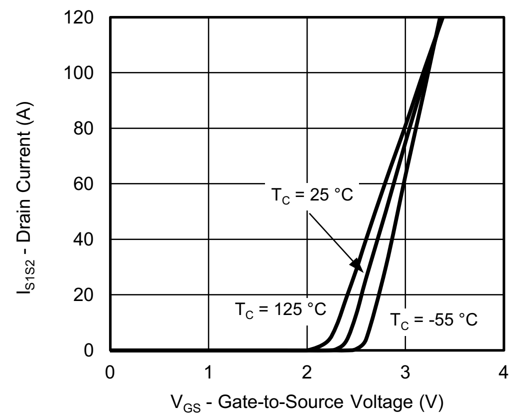
a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %
b. Guaranteed by design, not subject to production testing
c. On single MOSFET

*Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.*

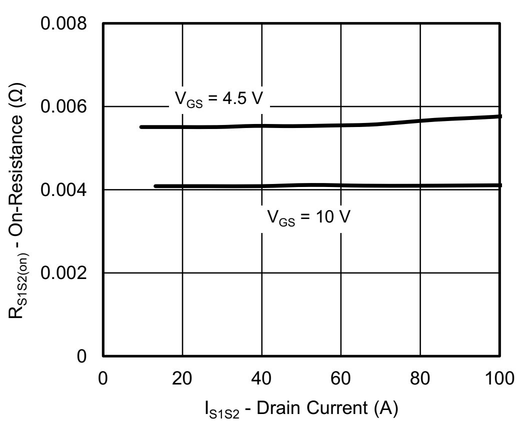
## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



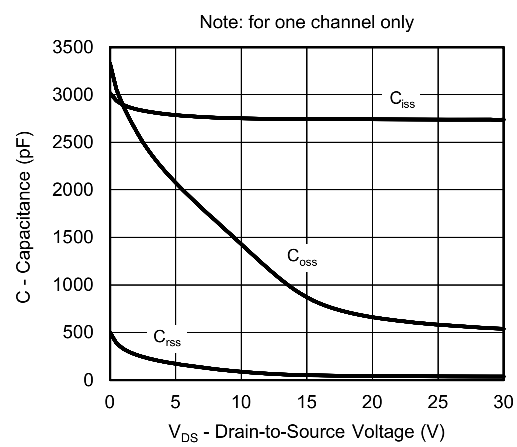

**Output Characteristics**



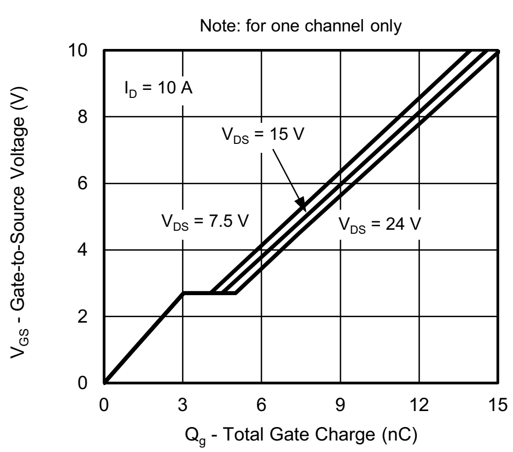

**Transfer Characteristics**



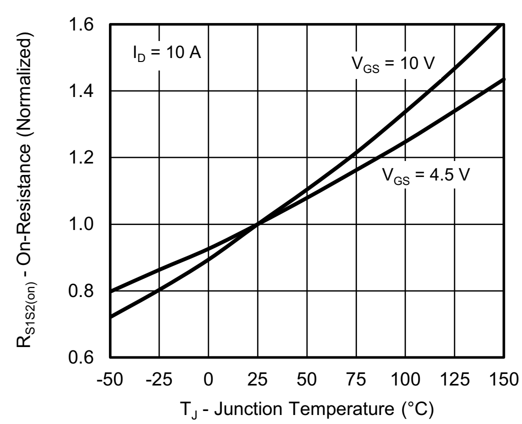

**On-Resistance vs. Drain Current and Gate Voltage**




**Capacitance**

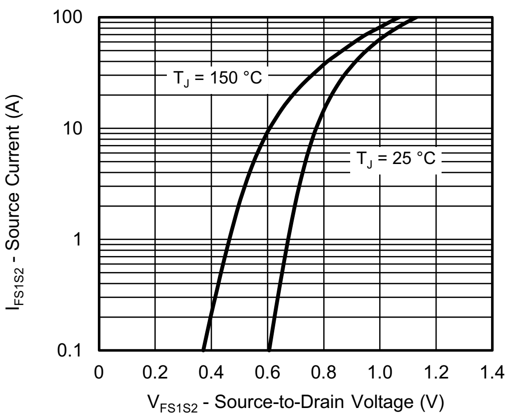



**Gate Charge**

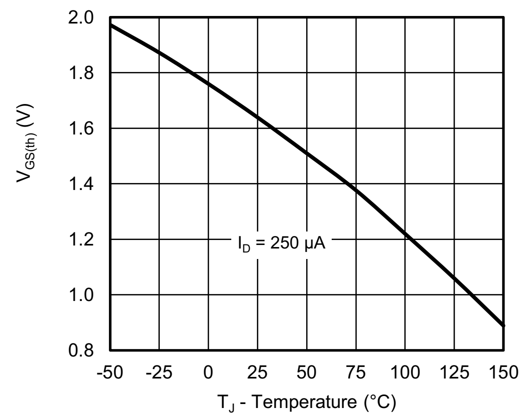



**On-Resistance vs. Junction Temperature**

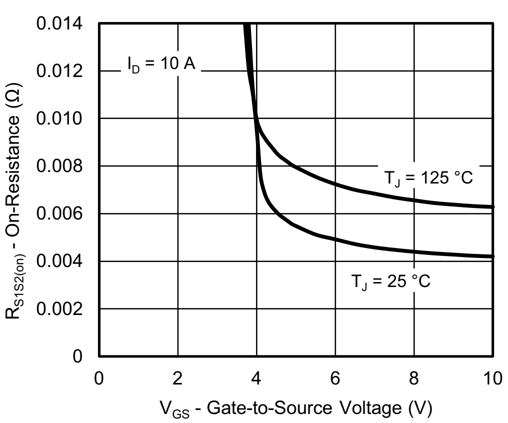
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



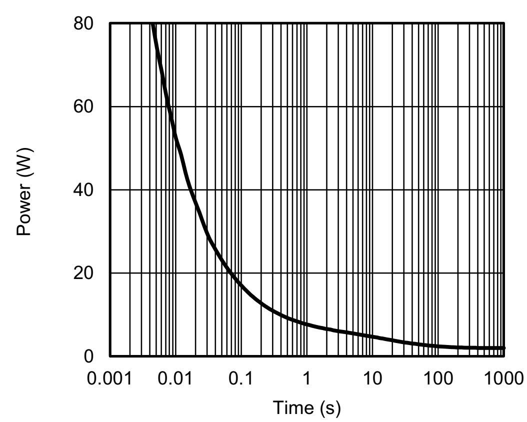

**Source-Drain Diode Forward Voltage**



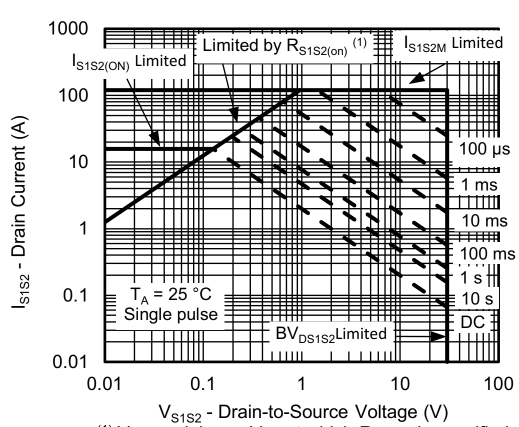

**Threshold Voltage**




**On-Resistance vs. Gate-to-Source Voltage**



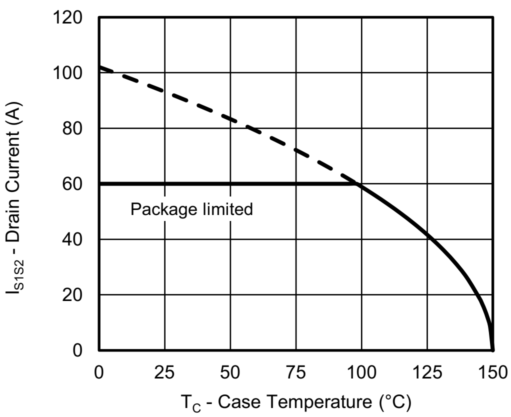

**Single Pulse Power, Junction-to-Ambient**



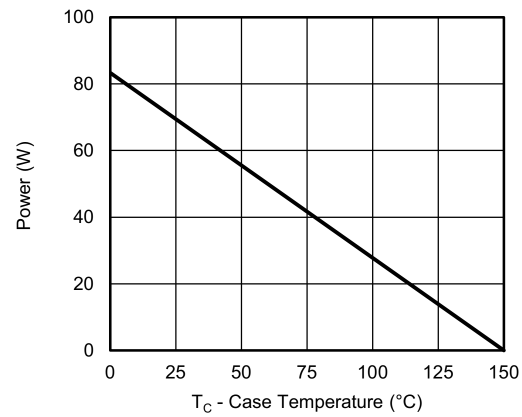

(1) $V_{GS}$ > minimum $V_{GS}$ at which $R_{DS(on)}$ is specified

**Safe Operating Area, Junction-to-Ambient**

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



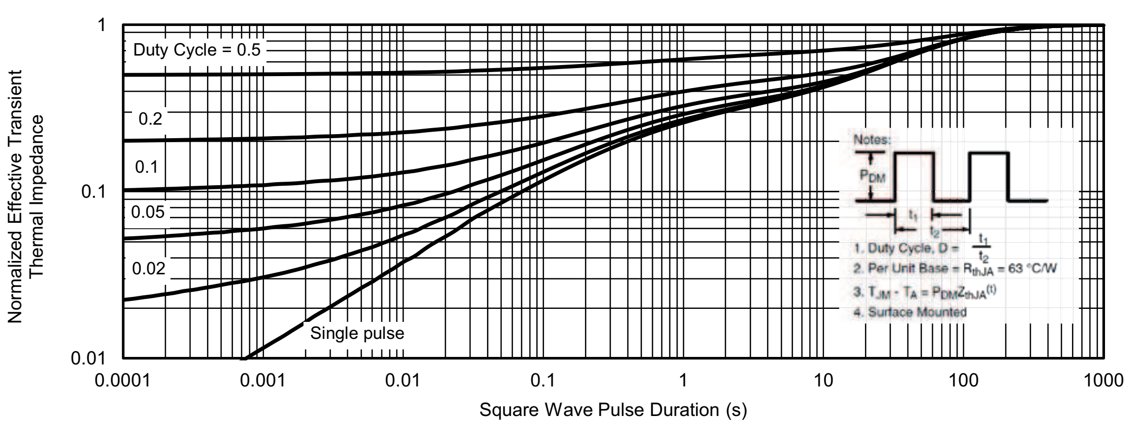

**Current Derating [a]**




**Power, Junction-to-Case (Drain)**

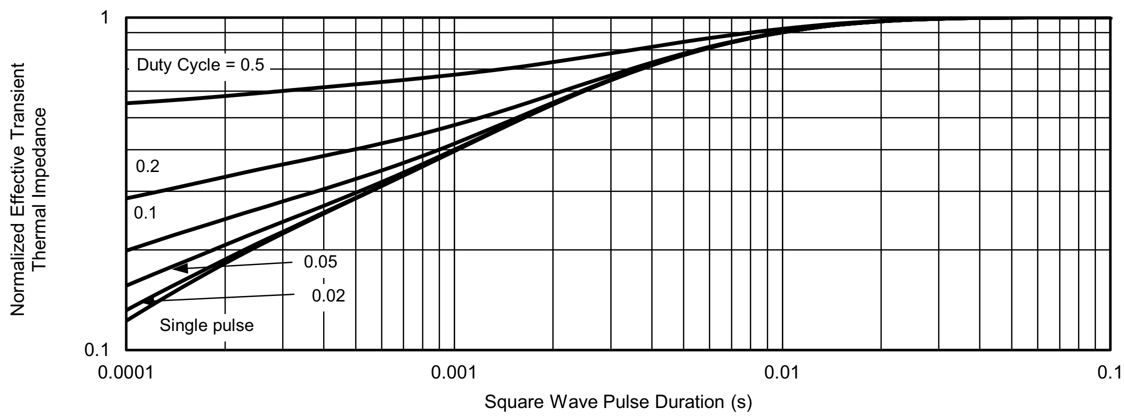
**Note**

a. The power dissipation $P_D$ is based on $T_J$ max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit




**Normalized Thermal Transient Impedance, Junction-to-Ambient**

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)




**Normalized Thermal Transient Impedance, Junction-to-Case (Drain)**

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